Abstracts

Low-Noise, Low DC Power Linear Amplifiers (1993 Vol. I [MWSYM])

P.K. Ikalainen, L.C. Witkowski and K.R. Varian. "Low-Noise, Low DC Power Linear Amplifiers (1993 Vol. I [MWSYM])." 1993 MTT-S International Microwave Symposium Digest 93.1 (1993 Vol. I [MWSYM]): 357-360.

Single and dual-gate distributed amplifiers designed for standard ion-implanted GaAs FETs and a newly designed Ku-band amplifier were processed using new high dynamic range FET process. State-of-the-art results were achieved in terms of simultaneous linearity, DC power, noise figure, and gain-bandwidth. OIP3/P/sub dc/ ratios of the amplifiers were in the range 1 to 13.7 with noise figures as low as 3 dB, 8 to 20 dB improvement in second-order linearity has been demonstrated as well.

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